



Schottky Diode

$V_{RRM} = 25\text{ V}$

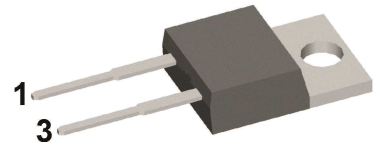
$I_{FAV} = 25\text{ A}$

$V_F = 0.45\text{ V}$

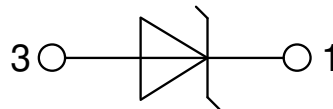
High Performance Schottky Diode
Low Loss and Soft Recovery
Single Diode

Part number

DSS25-0025B



Backside: cathode



Features / Advantages:

- Very low V_f
- Extremely low switching losses
- Low I_{rm} values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					25	V
V_{RRM}	max. repetitive reverse blocking voltage					25	V
I_R	reverse current, drain current	$V_R = 25\text{ V}$	$T_{VJ} = 25^\circ\text{C}$			20	mA
		$V_R = 25\text{ V}$	$T_{VJ} = 100^\circ\text{C}$			80	mA
V_F	forward voltage drop	$I_F = 25\text{ A}$	$T_{VJ} = 25^\circ\text{C}$			0.52	V
		$I_F = 50\text{ A}$				0.67	V
		$I_F = 25\text{ A}$	$T_{VJ} = 125^\circ\text{C}$			0.45	V
		$I_F = 50\text{ A}$				0.66	V
I_{FAV}	average forward current	$T_C = 125^\circ\text{C}$ rectangular	$T_{VJ} = 150^\circ\text{C}$ d = 0.5			25	A
V_{FO}	threshold voltage	} for power loss calculation only				0.21	V
r_F	slope resistance					8.8	mΩ
R_{thJC}	thermal resistance junction to case					1.4	K/W
R_{thCH}	thermal resistance case to heatsink				0.5		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		90	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; $V_R = 0\text{ V}$	$T_{VJ} = 45^\circ\text{C}$			330	A
C_J	junction capacitance	$V_R = 5\text{ V}$ f = 1 MHz	$T_{VJ} = 25^\circ\text{C}$		1.26		nF
E_{AS}	non-repetitive avalanche energy	$I_{AS} = 20\text{ A}$ L = 100 μH	$T_{VJ} = 25^\circ\text{C}$			60	mJ
I_{AR}	repetitive avalanche current	$V_A = 1.5 \cdot V_R$ typ. f = 10 kHz				2	A



Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{VJ}	virtual junction temperature		-55		150	°C
T_{op}	operation temperature		-55		125	°C
T_{stg}	storage temperature		-55		150	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N

Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSS25-0025B	DSS25-0025B	Tube	50	475114

Equivalent Circuits for Simulation

** on die level*

$T_{VJ} = 150^{\circ}C$

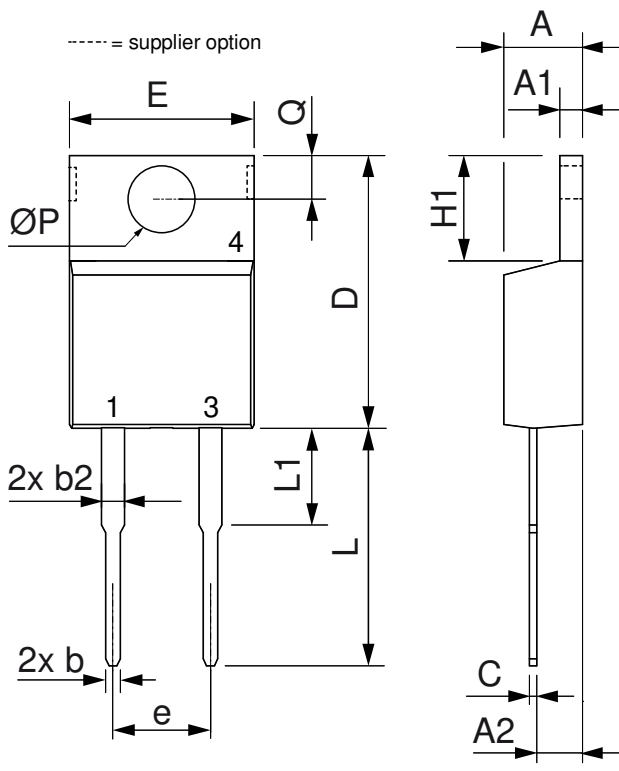


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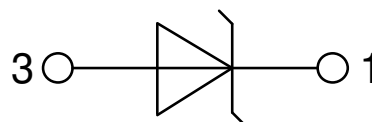
$V_{0\ max}$	threshold voltage	0.21	V
$R_{0\ max}$	slope resistance *	5.6	mΩ



Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



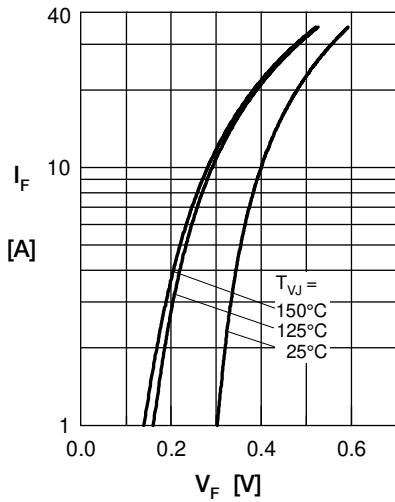
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Fig. 1 Max. forward voltage drop characteristics

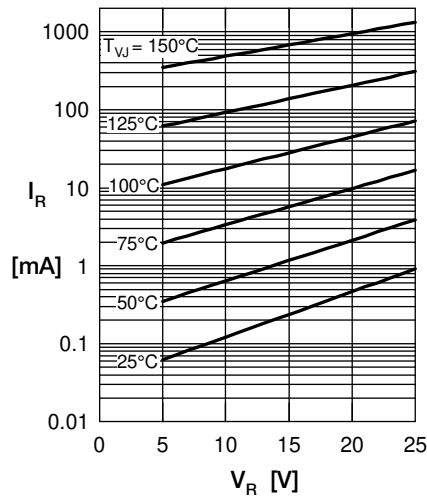
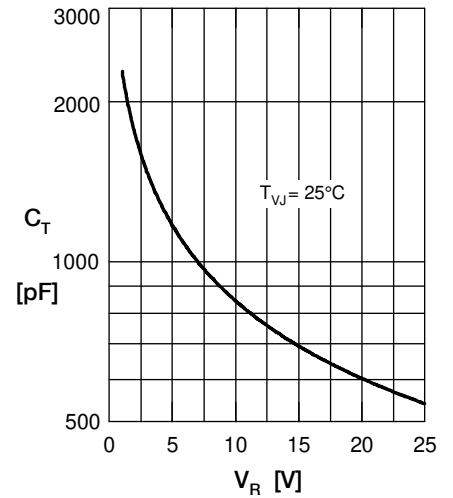
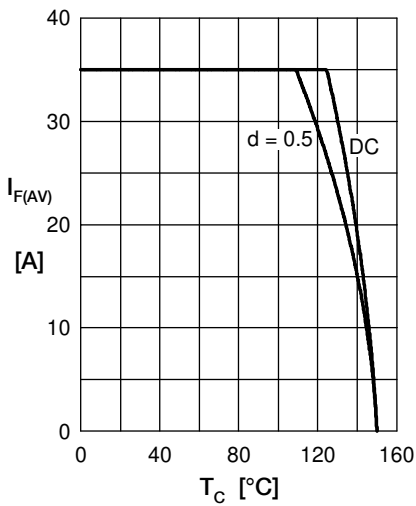
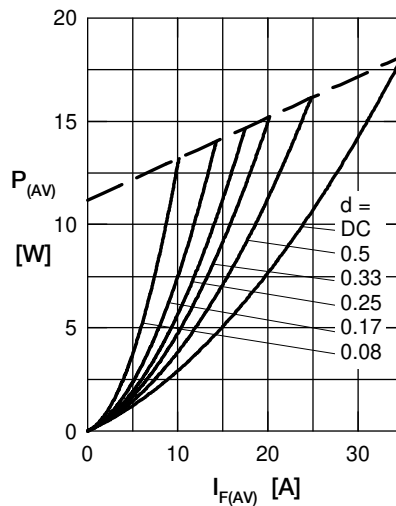

 Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

 Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

 Fig. 4 Average forward current $I_{F(AV)}$ vs. case temp. T_C


Fig. 5 Forward power loss characteristics

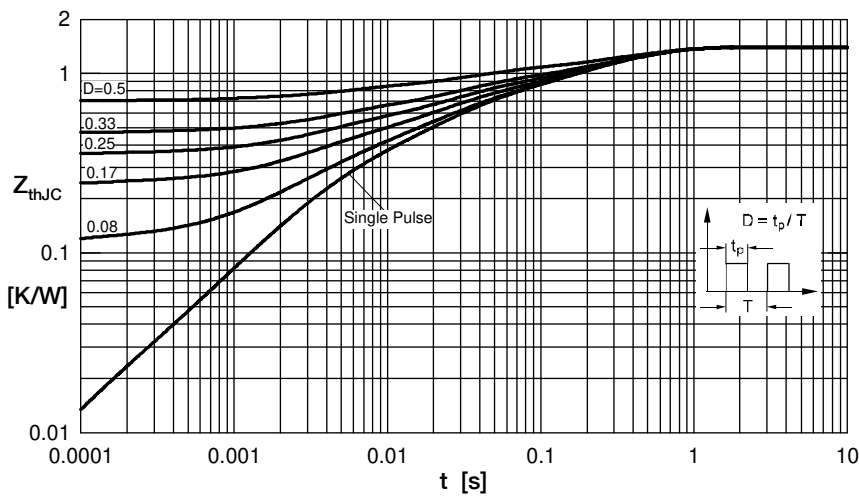


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode